



BUL742C

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

| Ordering Code | Marking | Package / Shipment |
|---------------|---------|--------------------|
| BUL742C | BUL742C | TO-220 / Tube |

- HIGH VOLTAGE CAPABILITY
- LOW SPREAD OF DYNAMIC PARAMETERS
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- VERY HIGH SWITCHING SPEED

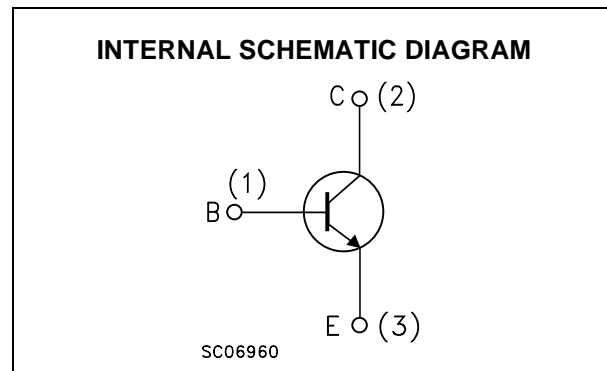
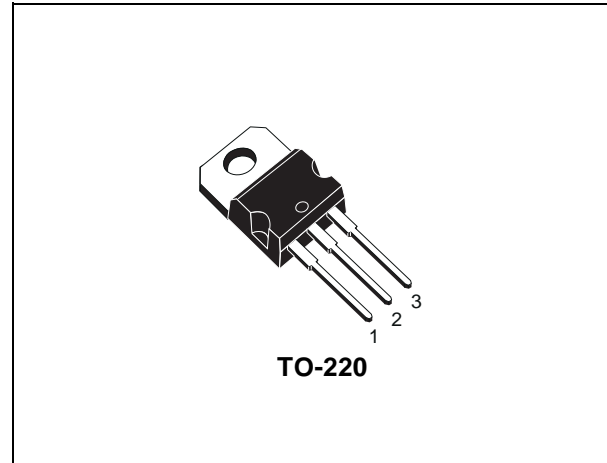
APPLICATIONS:

- ELECTRONIC BALLAST FOR FLUORESCENT LIGHTING
- SWITCH MODE POWER SUPPLIES

DESCRIPTION

The device is manufactured using High Voltage Multi Epitaxial Planar technology for high switching speeds and high voltage capability.

Thanks to an increased intermediate layer, it has an intrinsic ruggedness which enables the transistor to withstand an high collector current level during breakdown condition, without using the transil protection usually necessary in typical converters for lamp ballast.



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|-----------|--|---------------|------------------|
| V_{CES} | Collector-Emitter Voltage ($V_{BE} = 0$) | 1050 | V |
| V_{CEO} | Collector-Emitter Voltage ($I_B = 0$) | 400 | V |
| V_{EBO} | Emitter-Base Voltage ($I_C = 0, I_B < 2 \text{ A}, t_p < 10 \text{ ms}$) | $V_{(BR)EBO}$ | V |
| I_C | Collector Current | 4 | A |
| I_{CM} | Collector Peak Current ($t_p < 5 \text{ ms}$) | 8 | A |
| I_B | Base Current | 2 | A |
| I_{BM} | Base Peak Current ($t_p < 5 \text{ ms}$) | 4 | A |
| P_{tot} | Total Dissipation at $T_C = 25 \text{ }^\circ\text{C}$ | 70 | W |
| T_{stg} | Storage Temperature | -65 to 150 | $^\circ\text{C}$ |
| T_j | Max. Operating Junction Temperature | 150 | $^\circ\text{C}$ |

BUL742C

THERMAL DATA

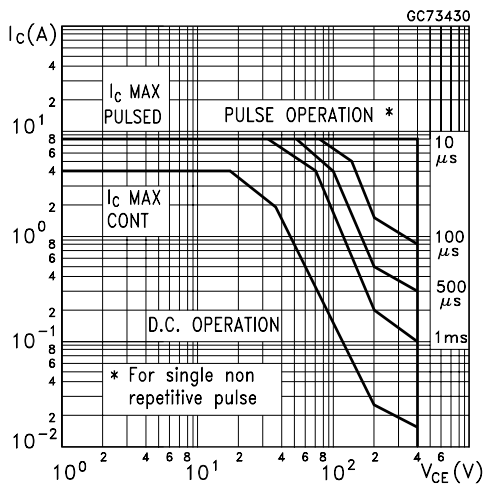
| | | | | |
|-----------------------|-------------------------------------|-----|------|------|
| R _{thj-case} | Thermal Resistance Junction-case | Max | 1.79 | °C/W |
| R _{thj-amb} | Thermal Resistance Junction-ambient | Max | 62.5 | °C/W |

ELECTRICAL CHARACTERISTICS (T_j = 25 °C unless otherwise specified)

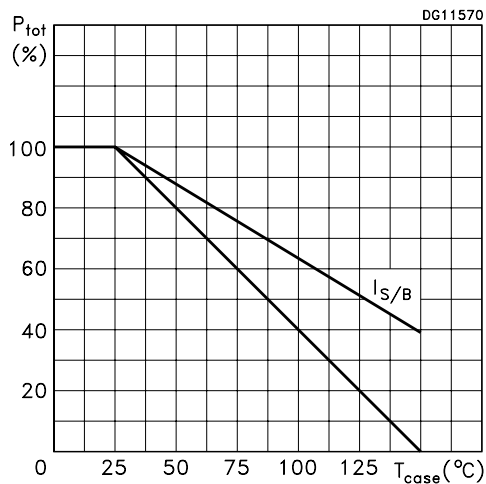
| Symbol | Parameter | Test Conditions | | Min. | Typ. | Max. | Unit |
|----------------------------------|---|--|--|----------|------------|------------|----------|
| I _{CES} | Collector Cut-off Current (V _{BE} = 0) | V _{CE} = 1050 V | | | | 100 | μA |
| I _{CEO} | Collector Cut-off Current (I _B = 0) | V _{CE} = 400 V | | | | 250 | μA |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage (I _C = 0) | I _E = 1 mA | | 12 | | 24 | V |
| V _{CEO(sus)} * | Collector-Emitter Sustaining Voltage (I _B = 0) | I _C = 10 mA | | 400 | | | V |
| V _{CE(sat)} * | Collector-Emitter Saturation Voltage | I _C = 1 A I _C = 3.5 A | I _B = 0.2 A I _B = 1 A | | | 0.5 1.5 | V V |
| V _{BE(sat)} * | Base-Emitter Saturation Voltage | I _C = 3.5 A | I _B = 1 A | | | 1.5 | V |
| h _{FE} * | DC Current Gain | I _C = 0.1 A I _C = 0.8 A | V _{CE} = 5 V V _{CE} = 3 V | 48 25 | | 100 50 | |
| t _s t _f | RESISTIVE LOAD Storage Time Fall Time | I _C = 2 A I _{B1} = -I _{B2} = 400 mA V _{BB(off)} = -5 V | V _{CC} = 125 V t _p = 300 μs (See Figure 1) | | 2.4 350 | | μs ns |
| E _{ar} | Repetitive Avalanche Energy | L = 2 mH V _{BE} = -5 V | C = 1.8 nF (See Figure 2) | 6 | | | mJ |

* Pulsed: Pulse duration = 300 μs, duty cycle = 1.5 %.

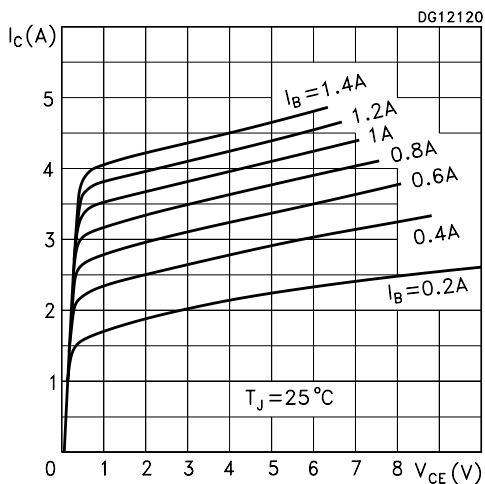
Safe Operating Area



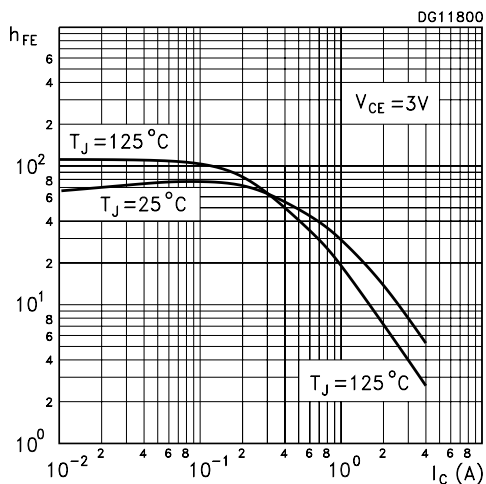
Derating Curve



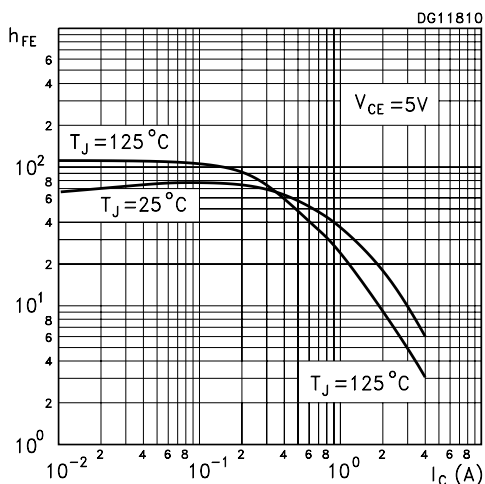
Output Characteristics



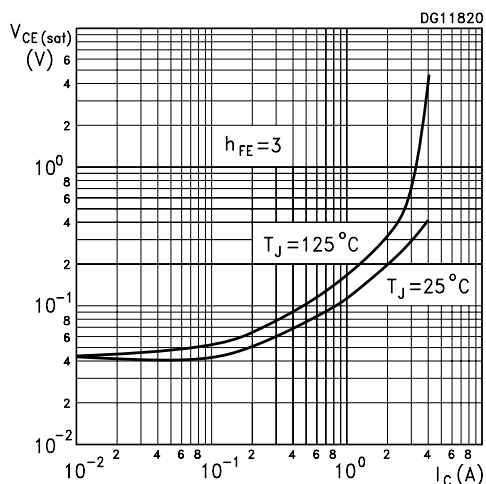
DC Current Gain



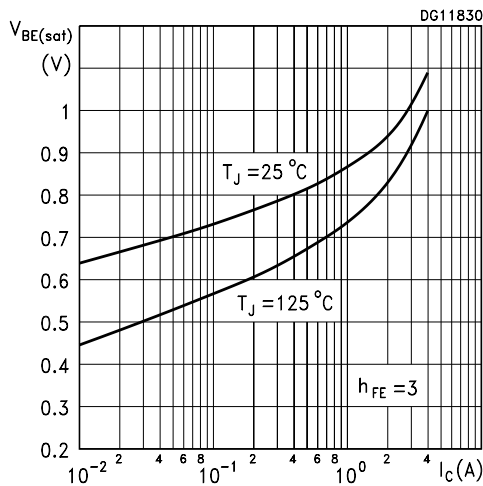
DC Current Gain



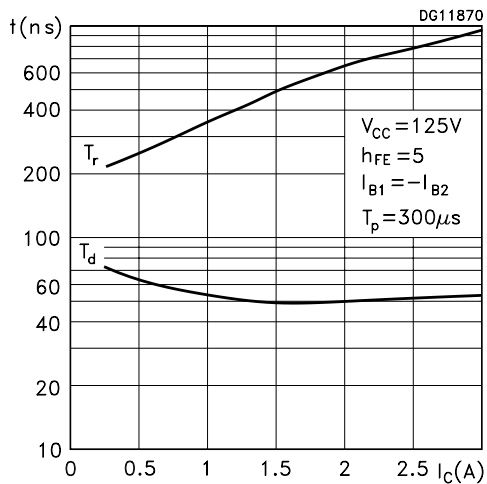
Collector-Emitter Saturation Voltage



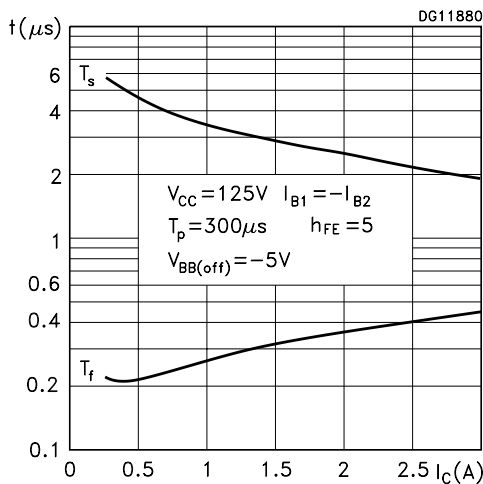
Base-Emitter Saturation Voltage



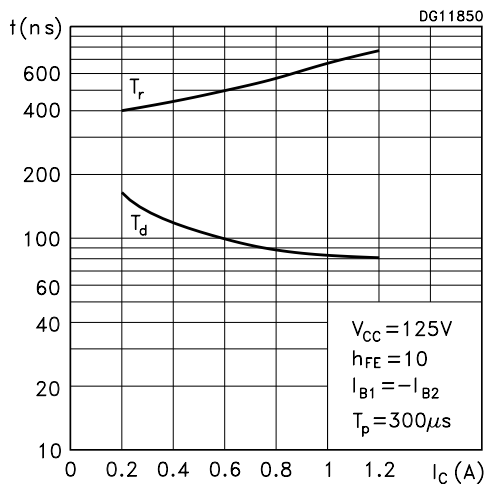
Resistive Load Switching On Times



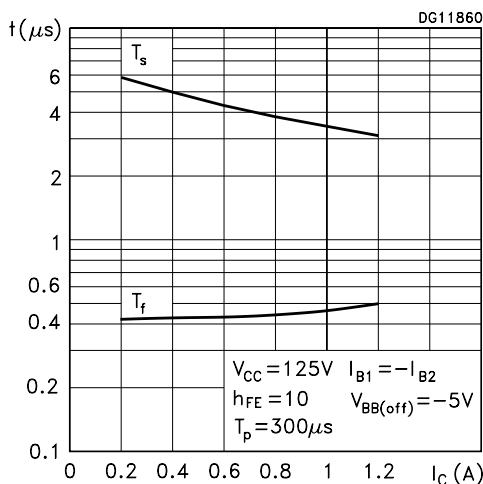
Resistive Load Switching Off Times



Resistive Load Switching On Times



Resistive Load Switching Off Times



Reverse Biased Safe Operating Area

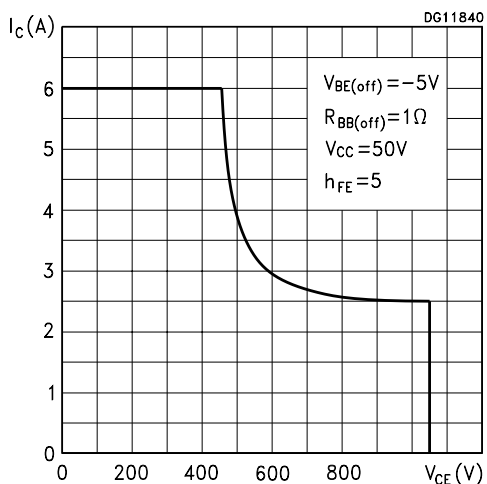


Figure 1: Resistive Load Switching Test Circuit

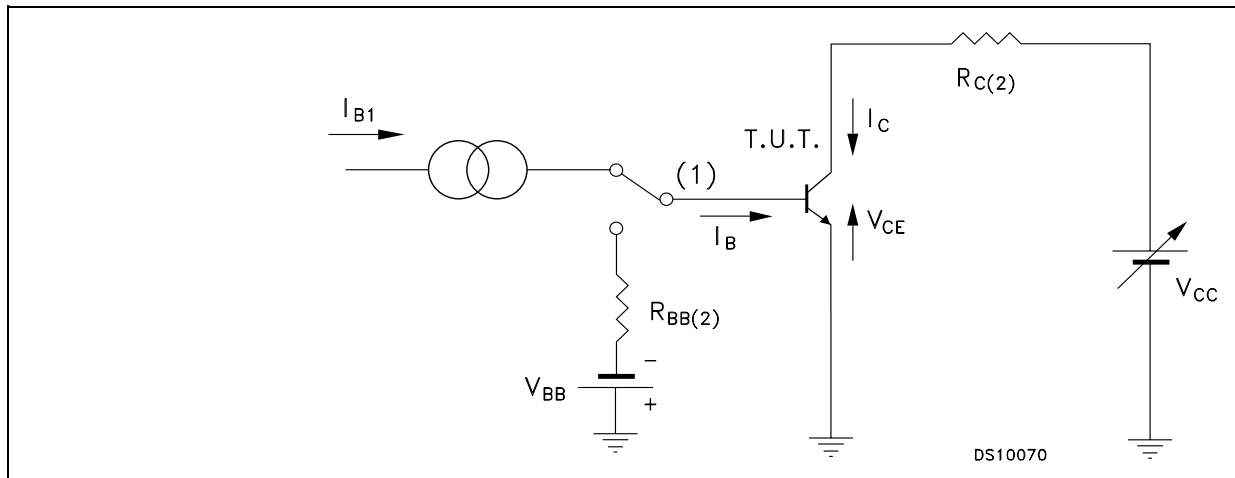
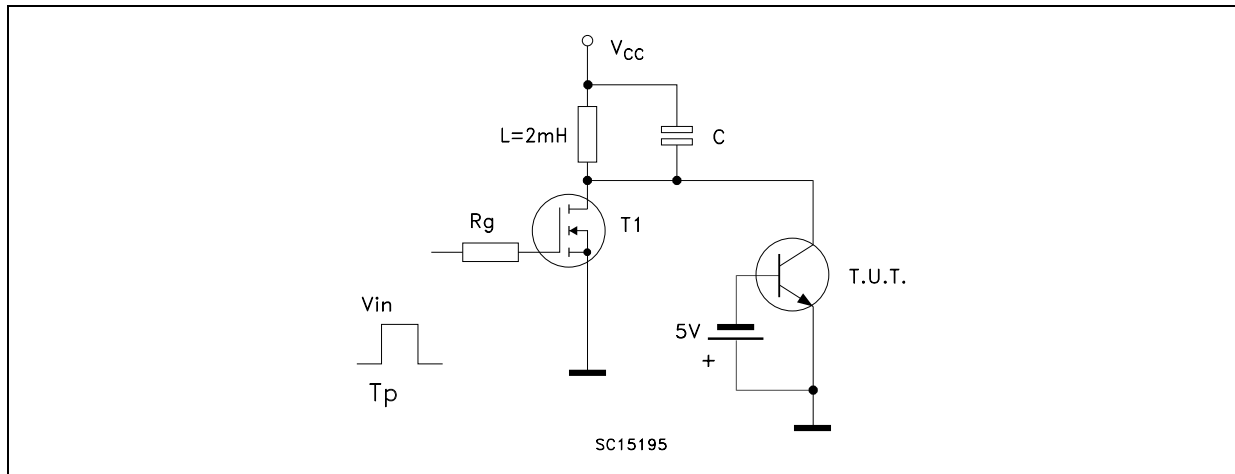
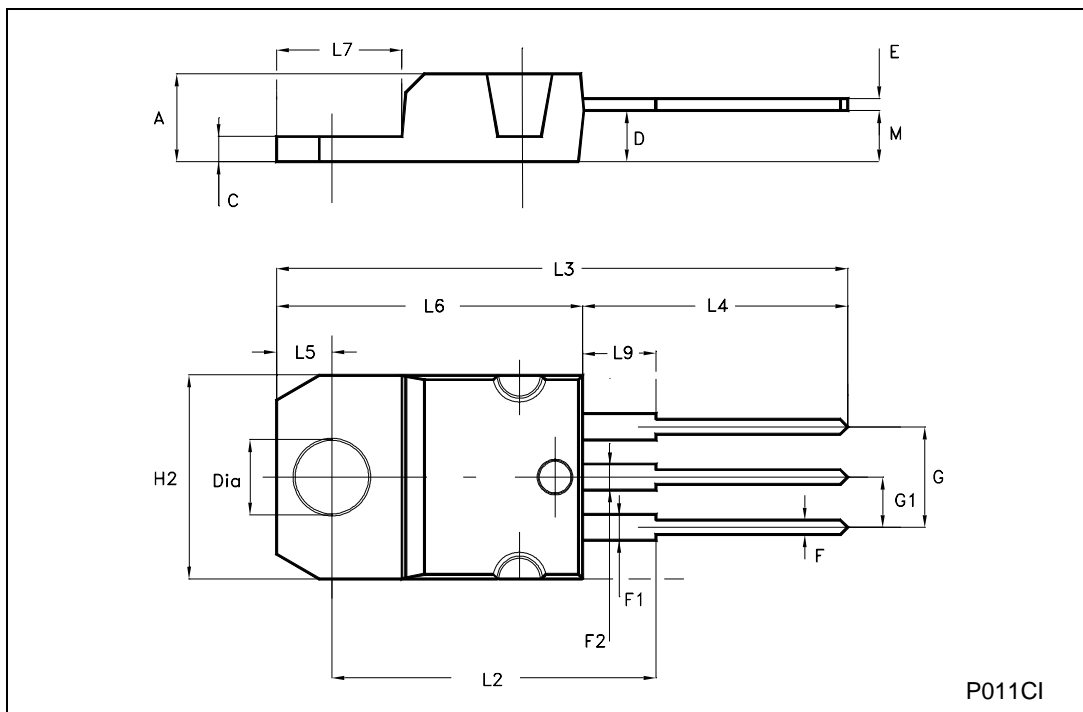


Figure 2: Energy Rating Test Circuit



TO-220 MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|-------|-------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 4.40 | | 4.60 | 0.173 | | 0.181 |
| C | 1.23 | | 1.32 | 0.048 | | 0.052 |
| D | 2.40 | | 2.72 | 0.094 | | 0.107 |
| E | 0.49 | | 0.70 | 0.019 | | 0.027 |
| F | 0.61 | | 0.88 | 0.024 | | 0.034 |
| F1 | 1.14 | | 1.70 | 0.044 | | 0.067 |
| F2 | 1.14 | | 1.70 | 0.044 | | 0.067 |
| G | 4.95 | | 5.15 | 0.194 | | 0.202 |
| G1 | 2.40 | | 2.70 | 0.094 | | 0.106 |
| H2 | 10.00 | | 10.40 | 0.394 | | 0.409 |
| L2 | | 16.40 | | | 0.645 | |
| L4 | 13.00 | | 14.00 | 0.511 | | 0.551 |
| L5 | 2.65 | | 2.95 | 0.104 | | 0.116 |
| L6 | 15.25 | | 15.75 | 0.600 | | 0.620 |
| L7 | 6.20 | | 6.60 | 0.244 | | 0.260 |
| L9 | 3.50 | | 3.93 | 0.137 | | 0.154 |
| M | | 2.60 | | | 0.102 | |
| DIA. | 3.75 | | 3.85 | 0.147 | | 0.151 |



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